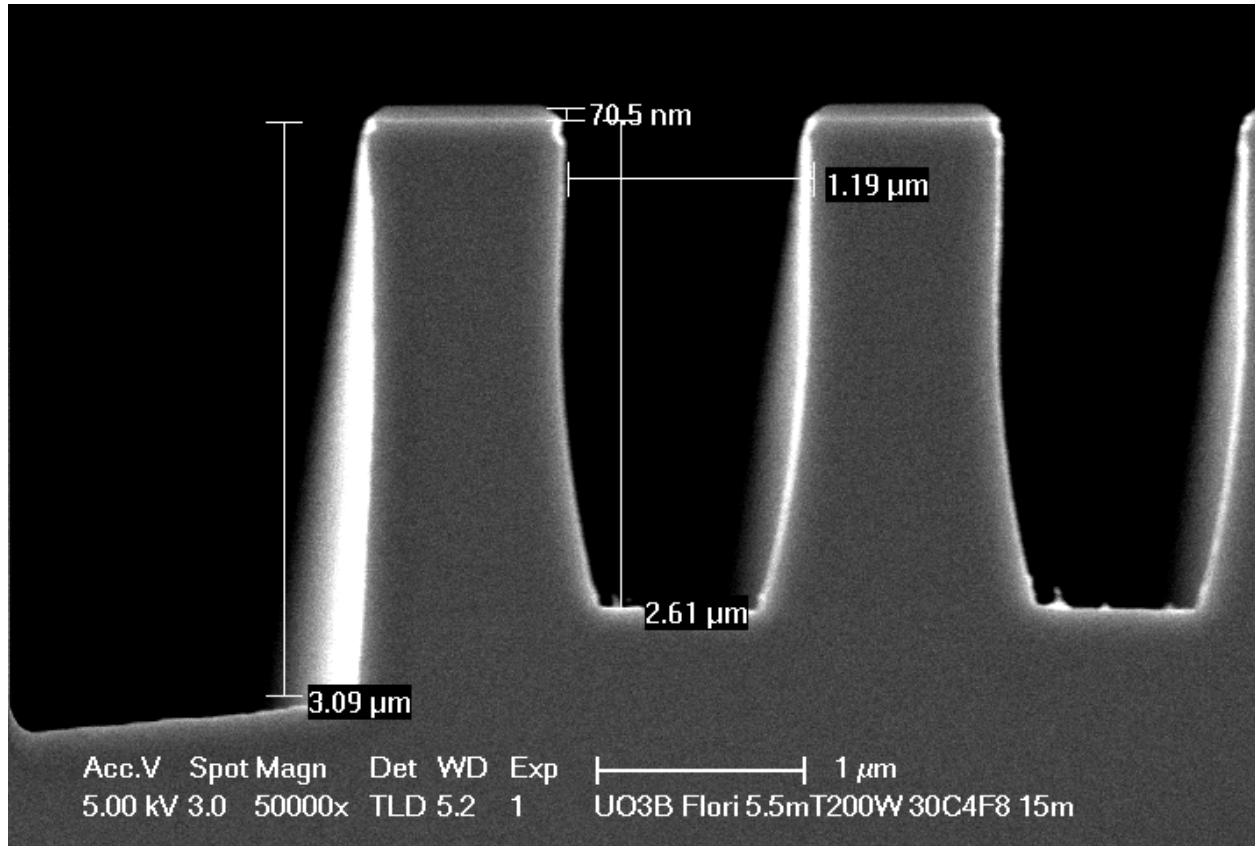


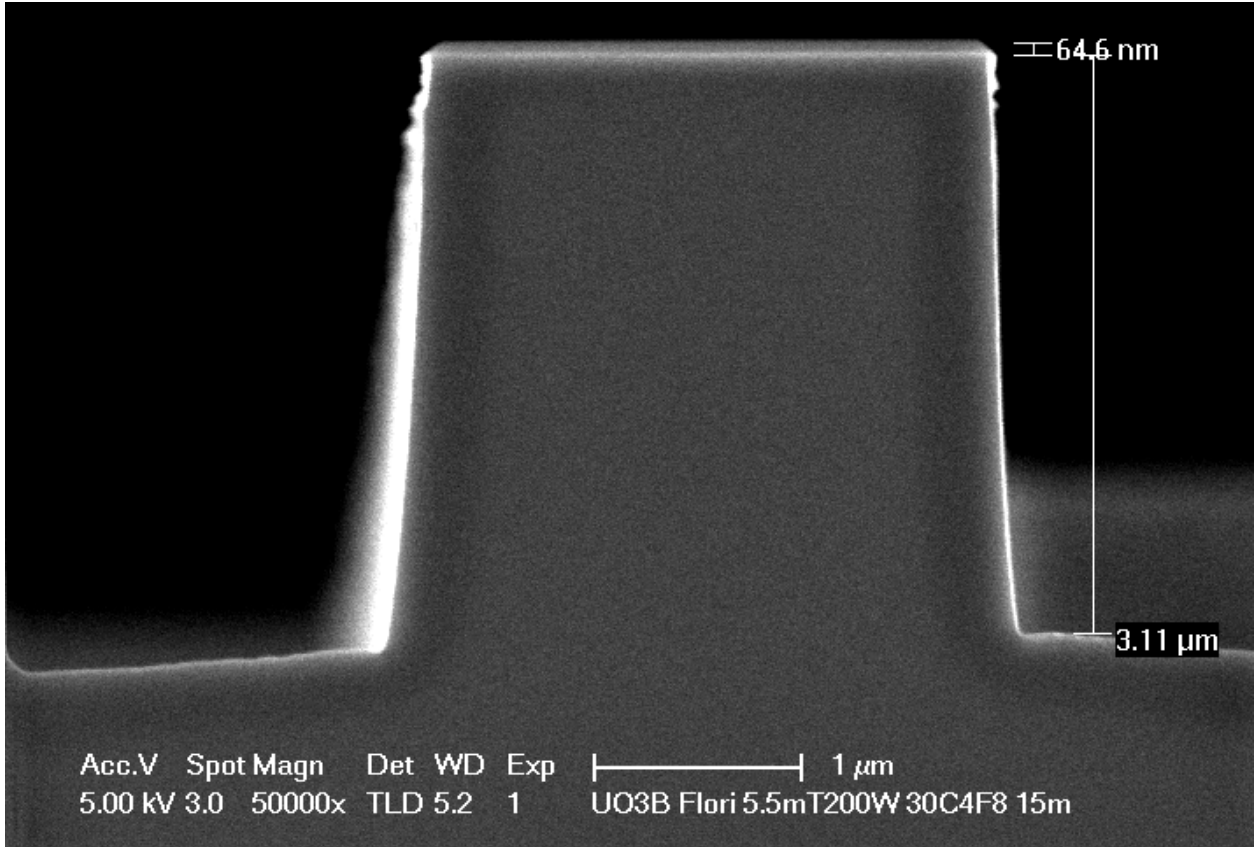
2022-01-11 DJ Cal – InP Ridge Process

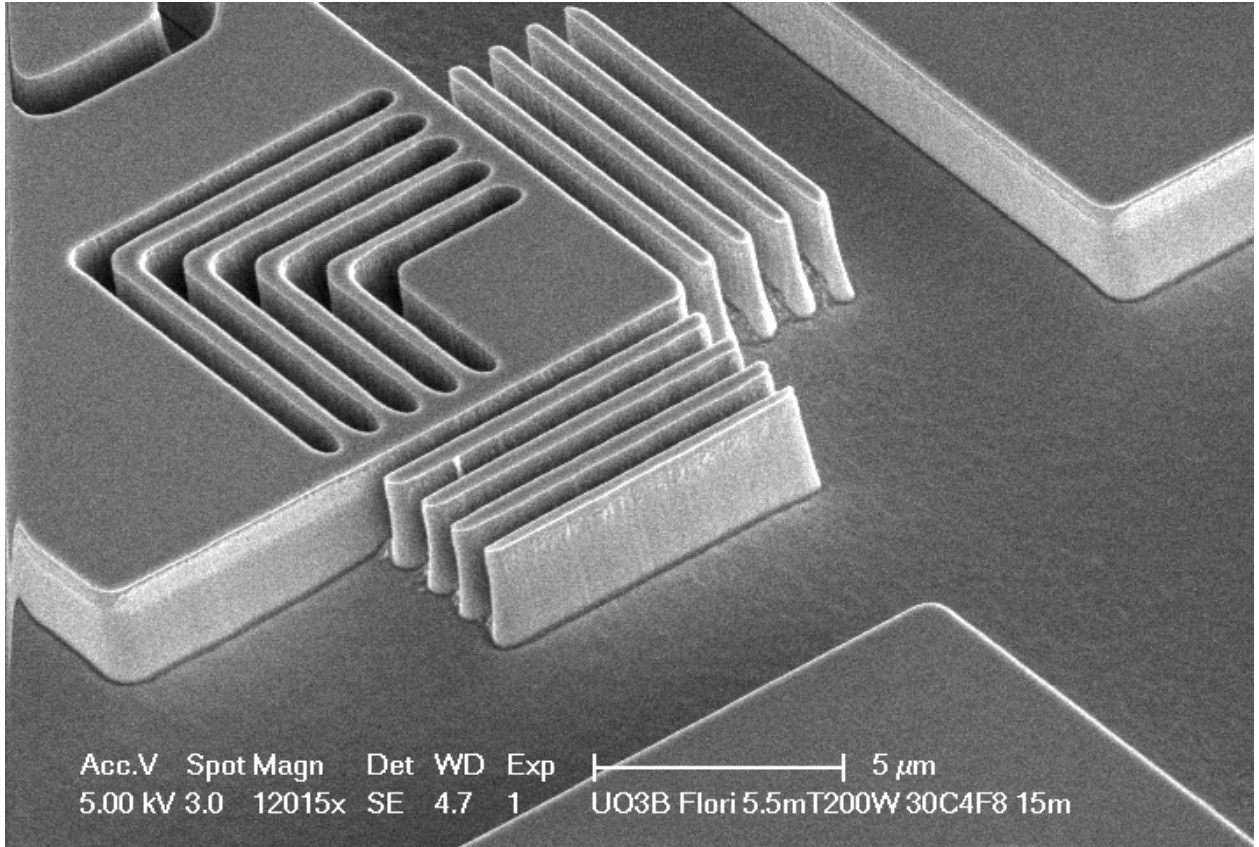
Ning's "InP Wafer" patterned samples

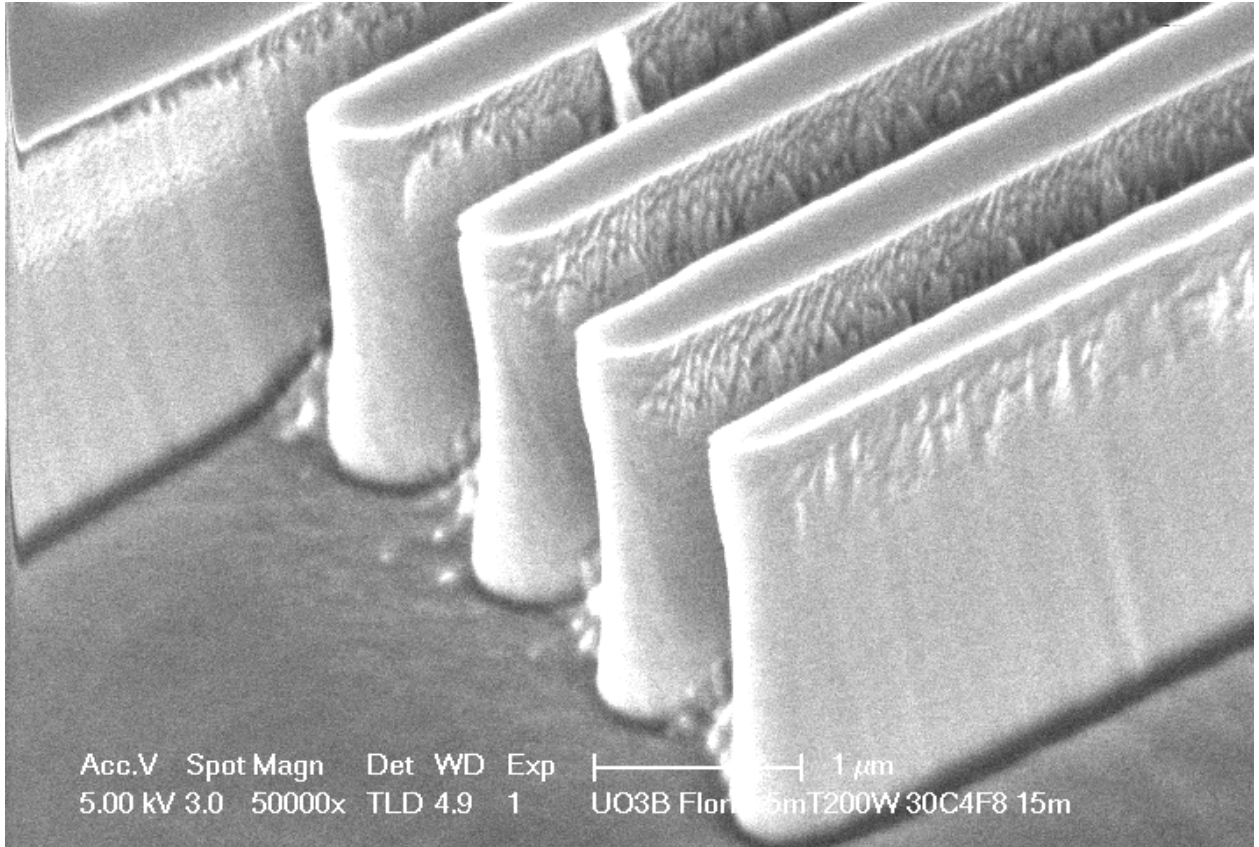
Oxford ICP "InP Ridge Etch":

3mT, 800W/65W, Cl<sub>2</sub>=18, H<sub>2</sub>=15, CH<sub>4</sub>=10sccm, time=5min05sec (305sec)









Acc.V Spot Magn Det WD Exp |-----| 1 μm  
5.00 kV 3.0 50000x TLD 4.9 1 UO3B Flor 5mT200W 30C4F8 15m